Xudong Wang

List of Publications by Year in descending order

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51 papers	3,093 citations	201674 27 h-index	189892 50 g-index
52 all docs	52 docs citations	52 times ranked	3940 citing authors

#	Article	IF	Citations
1	Effect of Aâ€site atom on static corrosion behavior and irradiation damage of Ti₂SC phases. Journal of the American Ceramic Society, 2022, 105, 1386-1393.	3.8	2
2	HgCdTe/black phosphorus van der Waals heterojunction for high-performance polarization-sensitive midwave infrared photodetector. Science Advances, 2022, 8, eabn1811.	10.3	50
3	Test of a Prototype Nb₃Sn Sextupole Coil for 45-GHz ECR Ion Source Using Mirror Structure. IEEE Transactions on Applied Superconductivity, 2021, 31, 1-5.	1.7	1
4	End-Bonded Contacts of Tellurium Transistors. ACS Applied Materials & Interfaces, 2021, 13, 7766-7772.	8.0	12
5	Gateâ€Tunable Photodiodes Based on Mixedâ€Dimensional Te/MoTe₂ Van der Waals Heterojunctions. Advanced Electronic Materials, 2021, 7, 2001066.	5.1	29
6	Interface engineering of ferroelectric-gated MoS2 phototransistor. Science China Information Sciences, 2021, 64, 1.	4.3	10
7	Ferroelectric-tuned van der Waals heterojunction with band alignment evolution. Nature Communications, 2021, 12, 4030.	12.8	79
8	Cryogenic Test Facility and the Indirect Pre-Cooling Method For HL-LHC MCBRD 4.5K Test At IMP. IEEE Transactions on Applied Superconductivity, 2021, 31, 1-5.	1.7	2
9	High-Performance Photodetectors with an Ultrahigh Photoswitching Ratio and a Very Fast Response Speed in Self-Powered Cu₂ZnSnS₄/CdS PN Heterojunctions. ACS Applied Electronic Materials, 2021, 3, 4135-4143.	4.3	10
10	Ultrasensitive negative capacitance phototransistors. Nature Communications, 2020, 11, 101.	12.8	124
11	Highly Sensitive InSb Nanosheets Infrared Photodetector Passivated by Ferroelectric Polymer. Advanced Functional Materials, 2020, 30, 2006156.	14.9	41
12	A versatile photodetector assisted by photovoltaic and bolometric effects. Light: Science and Applications, 2020, 9, 160.	16.6	56
13	Ultrabroadband Photodetectors up to 10.6 Âμm Based on 2D Fe₃O₄ Nanosheets. Advanced Materials, 2020, 32, e2002237.	21.0	57
14	MoTe₂ pâ€“n Homojunctions Defined by Ferroelectric Polarization. Advanced Materials, 2020, 32, e1907937.	21.0	115
15	Two-dimensional series connected photovoltaic cells defined by ferroelectric domains. Applied Physics Letters, 2020, 116, .	3.3	10
16	Programmable transition metal dichalcogenide homojunctions controlled by nonvolatile ferroelectric domains. Nature Electronics, 2020, 3, 43-50.	26.0	167
17	Extremely Low Dark Current MoS₂ Photodetector via 2D Halide Perovskite as the Electron Reservoir. Advanced Optical Materials, 2020, 8, 1901402.	7.3	55
18	Multifunctional MoS₂ Transistors with Electrolyte Gel Gating. Small, 2020, 16, e2000420.	10.0	23

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19	Ferroelectric Enhanced Performance of a GeSn/Ge Dual-Nanowire Photodetector. Nano Letters, 2020, 20, 3872-3879.	9.1	33
20	Ultrabroad-Spectrum Photodetectors: Multimechanism Synergistic Photodetectors with Ultrabroad Spectrum Response from 375 nm to 10 Âμm (Adv. Sci. 15/2019). Advanced Science, 2019, 6, 1970089.	11.2	2
21	Ferroelectric properties of gradient doped Y2O3:HfO2 thin films grown by pulsed laser deposition. Applied Physics Letters, 2019, 115, .	3.3	9
22	A study on ionic gated MoS2 phototransistors. Science China Information Sciences, 2019, 62, 1.	4.3	8
23	A gate-free MoS₂ phototransistor assisted by ferroelectrics. Journal of Semiconductors, 2019, 40, 092002.	3.7	10
24	Multimode Signal Processor Unit Based on the Ambipolar WSe₂â€“Cr Schottky Junction. ACS Applied Materials & Interfaces, 2019, 11, 38895-38901.	8.0	3
25	Ultrasensitive Hybrid MoS₂â€“ZnCdSe Quantum Dot Photodetectors with High Gain. ACS Applied Materials & Interfaces, 2019, 11, 23667-23672.	8.0	62
26	Largeâ€area high quality PtSe₂ thin film with versatile polarity. InformaÄ‹Ã-MateriÃ¡ly, 2019, 1, 260-267.	17.3	54
27	Multimechanism Synergistic Photodetectors with Ultrabroad Spectrum Response from 375 nm to 10 Âμm. Advanced Science, 2019, 6, 1901050.	11.2	52
28	Ultrahighâ€Detectivity Photodetectors with Van der Waals Epitaxial CdTe Singleâ€Crystalline Films. Small, 2019, 15, e1900236.	10.0	27
29	Controlled Doping of Waferâ€Scale PtSe₂ Films for Device Application. Advanced Functional Materials, 2019, 29, 1805614.	14.9	87
30	Optoelectronics: Highâ€Performance Photovoltaic Detector Based on MoTe₂/MoS₂ Van der Waals Heterostructure (Small 9/2018). Small, 2018, 14, 1870038.	10.0	7
31	Graphene Dirac point tuned by ferroelectric polarization field. Nanotechnology, 2018, 29, 134002.	2.6	15
32	Highâ€Performance Photovoltaic Detector Based on MoTe₂/MoS₂ Van der Waals Heterostructure. Small, 2018, 14, 1703293.	10.0	205
33	The ambipolar evolution of a high-performance WSe₂ transistor assisted by a ferroelectric polymer. Nanotechnology, 2018, 29, 105202.	2.6	20
34	Ferroelectric Localized Fieldâ€“Enhanced ZnO Nanosheet Ultraviolet Photodetector with High Sensitivity and Low Dark Current. Small, 2018, 14, e1800492.	10.0	85
35	Field Effect Transistors: Ferroelectric Negative Capacitance Field Effect Transistor (Adv. Electron.) Tj ETQq1 1 0.784314 rgBT /Overloc	5.1	7
36	High-performance lead-free two-dimensional perovskite photo transistors assisted by ferroelectric dielectrics. Journal of Materials Chemistry C, 2018, 6, 12714-12720.	5.5	39

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37	Ultrahigh photoresponsivity MoS₂ photodetector with tunable photocurrent generation mechanism. Nanotechnology, 2018, 29, 485204.	2.6	35
38	Ferroelectric Negative Capacitance Field Effect Transistor. Advanced Electronic Materials, 2018, 4, 1800231.	5.1	105
39	High performance top-gated ferroelectric field effect transistors based on two-dimensional ZnO nanosheets. Applied Physics Letters, 2017, 110, .	3.3	34
40	Recent Progress on Localized Field Enhanced Twoâ€dimensional Material Photodetectors from Ultravioletâ€"Visible to Infrared. Small, 2017, 13, 1700894.	10.0	234
41	Two-dimensional negative capacitance transistor with polyvinylidene fluoride-based ferroelectric polymer gating. Npj 2D Materials and Applications, 2017, 1, .	7.9	77
42	Electrical characterization of MoS2 field-effect transistors with different dielectric polymer gate. AIP Advances, 2017, 7, .	1.3	15
43	Ferroelectric polymer tuned two dimensional layered MoTe₂ photodetector. RSC Advances, 2016, 6, 87416-87421.	3.6	51
44	Optoelectronic Properties of Few-Layer MoS₂ FET Gated by Ferroelectric Relaxor Polymer. ACS Applied Materials & Interfaces, 2016, 8, 32083-32088.	8.0	76
45	Novel graphene field effect transistor with BNTM ferroelectric gate. , 2016, , .		0
46	Flexible graphene field effect transistor with ferroelectric polymer gate. Optical and Quantum Electronics, 2016, 48, 1.	3.3	21
47	When Nanowires Meet Ultrahigh Ferroelectric Fieldâ€"High-Performance Full-Depleted Nanowire Photodetectors. Nano Letters, 2016, 16, 2548-2555.	9.1	135
48	Photodetectors: Ultrasensitive and Broadband MoS₂ Photodetector Driven by Ferroelectrics (Adv. Mater. 42/2015). Advanced Materials, 2015, 27, 6538-6538.	21.0	8
49	High temperature coefficient of resistance for a ferroelectric tunnel junction. Applied Physics Letters, 2015, 107, 062904.	3.3	3
50	Ultrasensitive and Broadband MoS₂ Photodetector Driven by Ferroelectrics. Advanced Materials, 2015, 27, 6575-6581.	21.0	722
51	Ferroelectric control of magnetism in P(VDFâ€"TrFE)/Co heterostructure. Journal of Materials Science: Materials in Electronics, 2015, 26, 7502-7506.	2.2	9